Integrated Device Technology, Inc.

CMOS DUAL-PORT RAMS 32K (2K x 16-BIT)

PRELIMINARY
IDT 7133S/L
IDT 7143S/L

FEATURES:

- High-speed access
  - Military: 55/70/90ns (max.)
  - Commercial: 45/55/70/90ns (max.)
- Low-power operation
  - IDT7133/43S
    Active: 375mW (typ.)
    Standby: 5mW (typ.)
  - IDT7133/43L
    Active: 375mW (typ.)
    Standby: 1mW (typ.)
- Versatile control for write: separate write control for lower and upper byte of each port
- MASTER IDT7133 easily expands data bus width to 32 bits or more using SLAVE IDT7143
- On-chip port arbitration logic (IDT7133 only)
- $\overline{BUSY}$ output flag on IDT7133; $\overline{BUSY}$ input on IDT7143
- Fully asynchronous operation from either port
- Battery backup operation – 2V data retention
- TTL-compatible, single 5V (±10%) power supply
- Available in 68-pin ceramic or plastic PGA, DIP (600 mil, 70 mil centers), LCC and PLCC
- Military product compliant to MIL-STD-883, Class B

DESCRIPTION:

The IDT7133/7143 are high-speed 2K x 16 dual-port static RAMs. The IDT7133 is designed to be used as a stand-alone 16-bit dual-port RAM or as a "MASTER" dual-port RAM together with the IDT7143 "SLAVE" dual-port in 32-bit-or-more word width systems. Using the IDT MASTER/SLAVE dual-port RAM approach in 32-bit-or-wider memory system applications results in full-speed, error-free operation without the need for additional discrete logic.

Both devices provide two independent ports with separate control, address and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature, controlled by $\overline{CE}$, permits the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using IDT's CEMOS™ high-performance technology, these devices typically operate on only 375mW of power at maximum access times as fast as 45ns. Low-power (L) versions offer battery backup data retention capability, with each port typically consuming 1mW from a 2V battery.

The IDT7133/7143 devices have identical pinouts. Each is packaged in a 68-pin ceramic or plastic PGA, 68-pin LCC, 68-pin PLCC, and 70 mil center DIPs.

Military grade product is manufactured in compliance with the latest revision of MIL-STD-883, Class B, making it ideally suited to military temperature applications demanding the highest level of performance and reliability.

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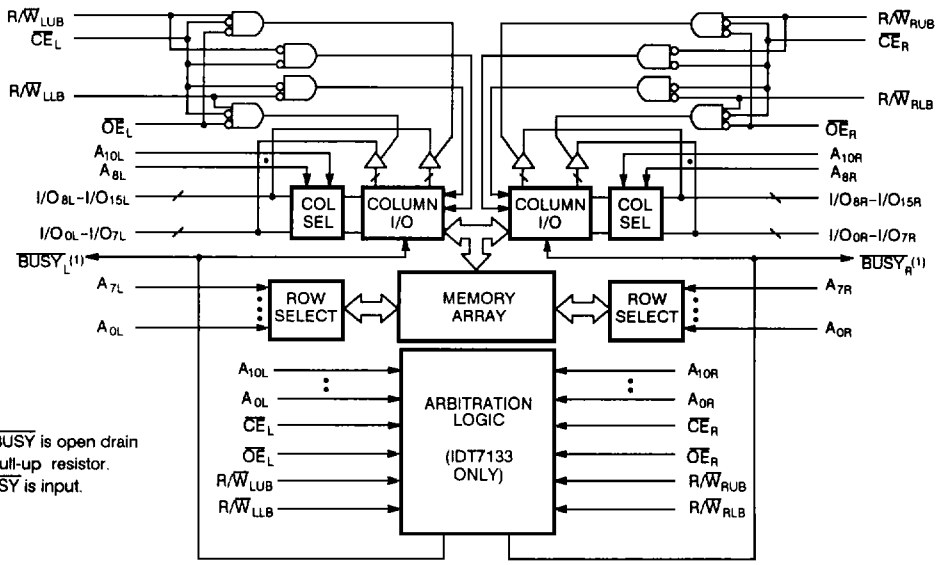
FUNCTIONAL BLOCK DIAGRAM



NOTES:

1. IDT7133 (MASTER): $\overline{BUSY}$ is open drain output and requires pull-up resistor.
   IDT7143 (SLAVE): $\overline{BUSY}$ is input.
2. LB = LOWER BYTE
   UB = UPPER BYTE

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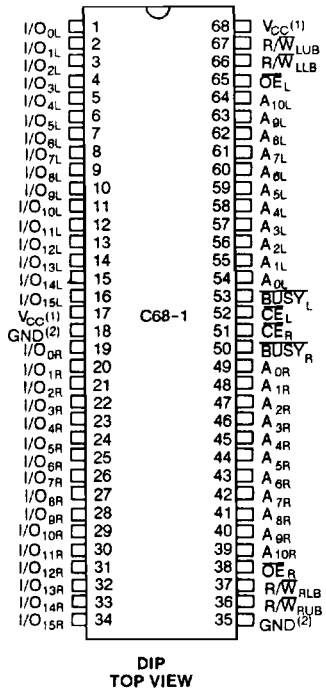
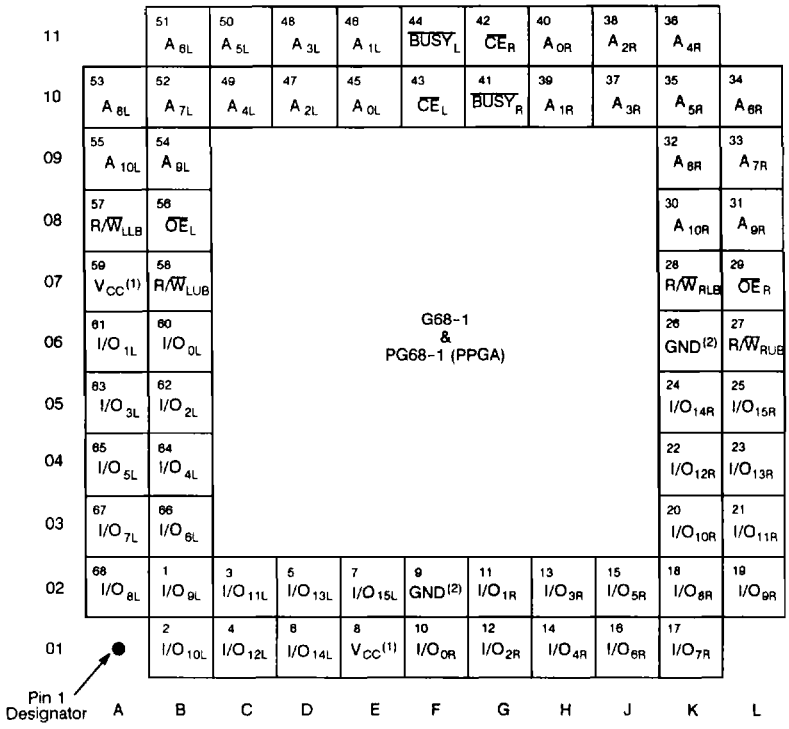
PIN CONFIGURATIONS



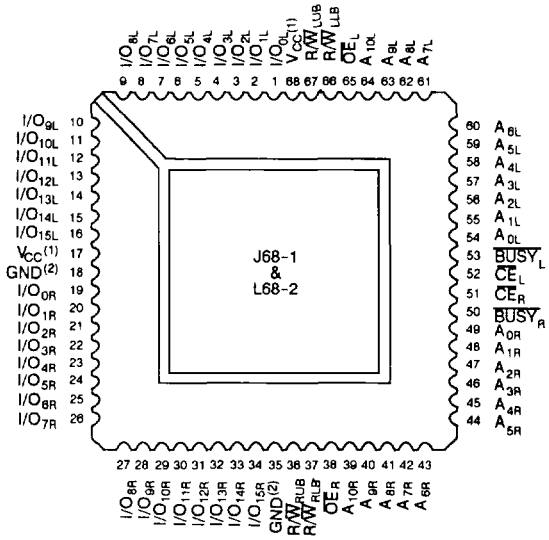
DIP
TOP VIEW



PGA TOP VIEW (Ceramic or Plastic)

NOTES:

1. Both V_{CC} pins must be connected to the supply to assure reliable operation.
2. Both GND pins must be connected to the supply to assure reliable operation.
3. UB = Upper Byte, LB = Lower Byte.



LCC/PLCC
TOP VIEW

ABSOLUTE MAXIMUM RATINGS [1]

SYMBOL	RATING	COMMERCIAL	MILITARY	UNIT
V_{TERM}	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
T_A	Operating Temperature	0 to +70	-55 to +125	°C
T_{BIAS}	Temperature Under Bias	-55 to +125	-65 to +135	°C
T_{STG}	Storage Temperature	-55 to +125	-65 to +150	°C
P_T	Power Dissipation	2.0	2.0	W
I_{OUT}	DC Output Current	50	50	mA

NOTE:

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

RECOMMENDED DC OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{CC}	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
V_{IH}	Input High Voltage	2.2	–	6.0	V
V_{IL}	Input Low Voltage	-0.5[1]	–	0.8	V

NOTE:

1. V_{IL} (min.) = -3.0V for pulse width less than 20ns.

RECOMMENDED OPERATING TEMPERATURE AND SUPPLY VOLTAGE

GRADE	AMBIENT TEMPERATURE	GND	V_{CC}
Military	-55°C to +125°C	0V	5.0V ± 10%
Commercial	0°C to +70°C	0V	5.0V ± 10%

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DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE (Either port, V_{CC} = 5.0V ±10%)

SYMBOL	PARAMETER	TEST CONDITIONS	IDT7133S IDT7143S MIN.	IDT7133S IDT7143S MAX.	IDT7133L IDT7143L MIN.	IDT7133L IDT7143L MAX.	UNIT
$\|I_{LI}\|$	Input Leakage Current	V_{CC} = 5.5V, V_{IN} = 0V to V_{CC}	–	10	–	5	µA
$\|I_{LO}\|$	Output Leakage Current	$\overline{CE}$ = V_{IH}, V_{OUT} = 0V to V_{CC}	–	10	–	5	µA
V_{OL}	Output Low Voltage (I/O_0 - I/O_{15})	I_{OL} = 4mA	–	0.4	–	0.4	V
V_{OL}	Open Drain Output Low Voltage ($\overline{BUSY}$)	I_{OL} = 16mA	–	0.5	–	0.5	V
V_{OH}	Output High Voltage	I_{OH} = -4mA	2.4	–	2.4	–	V

DC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE RANGE [3] (V_{CC} = 5.0V ±10%)

SYMBOL	PARAMETER	TEST CONDITION	VERSION		IDT7133x45 [1] IDT7143x45 [1] TYP.[2]	IDT7133x45 [1] IDT7143x45 [1] MAX.	IDT7133x55 IDT7143x55 TYP.[2]	IDT7133x55 IDT7143x55 MAX.	IDT7133x70 IDT7143x70 TYP.[2]	IDT7133x70 IDT7143x70 MAX.	IDT7133x90 IDT7143x90 TYP.[2]	IDT7133x90 IDT7143x90 MAX.	UNIT
I_{CC}	Dynamic Operating Current (Both Ports Active)	$\overline{CE}$ = V_{IL} Outputs Open f = f_{MAX} [4]	MIL.	S	–	–	–	280	75	260	75	260	mA
				L	–	–	–	260	75	240	75	240	
			COM'L.	S	–	260	75	240	75	240	75	235	
				L	–	240	75	220	75	220	75	215	
I_{SB1}	Standby Current (Both Ports – TTL Level Inputs)	$\overline{CE}_L$ and $\overline{CE}_R \geq V_{IH}$ f = f_{MAX} [4]	MIL.	S	–	–	–	80	25	75	25	75	mA
				L	–	–	–	70	25	65	25	65	
			COM'L.	S	–	75	25	70	25	70	25	65	
				L	–	65	25	60	25	60	25	55	
I_{SB2}	Standby Current (One Port – TTL Level Inputs)	$\overline{CE}_L$ or $\overline{CE}_R \geq V_{IH}$ f = f_{MAX} [4] Active Port Outputs Open	MIL.	S	–	–	–	180	50	170	50	170	mA
				L	–	–	–	160	50	150	50	150	
			COM'L.	S	–	160	50	150	50	150	50	145	
				L	–	140	50	130	50	130	50	125	
I_{SB3}	Full Standby Current (Both Ports – CMOS Level Inputs)	Both Ports $\overline{CE}_L$ and $\overline{CE}_R \geq V_{CC}$ -0.2V $V_{IN} \geq V_{CC}$ -0.2V or $V_{IN} \leq$ 0.2V f = 0 [5]	MIL.	S	–	–	–	30	1	30	1	30	mA
				L	–	–	–	10	0.2	10	0.2	10	
			COM'L.	S	–	15	1	15	1	15	1	15	
				L	–	4	0.2	4	0.2	4	0.2	4	
I_{SB4}	Full Standby Current (One Port – All CMOS Level Inputs, f = 0 [5])	One Port $\overline{CE}_L$ or $\overline{CE}_R \geq V_{CC}$ -0.2V $V_{IN} \geq V_{CC}$ -0.2V or $V_{IN} \leq$ 0.2V Active Port Outputs Open, f = f_{MAX} [4]	MIL.	S	–	–	–	170	45	160	45	155	mA
				L	–	–	–	150	40	140	40	135	
			COM'L.	S	–	150	45	140	45	140	45	135	
				L	–	130	40	120	40	120	40	115	

NOTES:

1. 0°C to +70°C temperature range only.
2. V_{CC} = 5V, T_A = +25°C
3. "x" in part numbers indicates power rating (S or L).
4. At f = f_{MAX}, address and data inputs (except Output Enable) are cycling at the maximum frequency of read cycle of $1/t_{RC}$, and using "AC TEST CONDITIONS" of input levels of GND to 3V.
5. f = 0 means no address or control lines change. Applies only to inputs at CMOS level standby.

DATA RETENTION CHARACTERISTICS OVER ALL TEMPERATURE RANGES [1]

(L Version Only) V_{LC} = 0.2V, V_{HC} = V_{CC} - 0.2V

SYMBOL	PARAMETER	TEST CONDITION		IDT7133S/L/IDT7143S/L MIN.	MAX.	UNIT
V_{DR}	V_{CC} for Data Retention	V_{CC} = 2.0V $\overline{CE} \geq V_{HC}$ $V_{IN} \geq V_{HC}$ or $\leq V_{LC}$		2.0	–	V
I_{CCDR}	Data Retention Current		MIL.	–	4000	µA
			COM'L.	–	1500	µA
t_{CDR}[3]	Chip Deselect to Data Retention Time			0	–	ns
t_R[3]	Operation Recovery Time			t_{RC}[2]	–	ns
I_{LI}[3]	Input Leakage Current			–	2	µA

NOTES:
1. V_{CC} = 2V, T_A = +25°C.
2. t_{RC} = Read Cycle Time.
3. This parameter is guaranteed but not tested.

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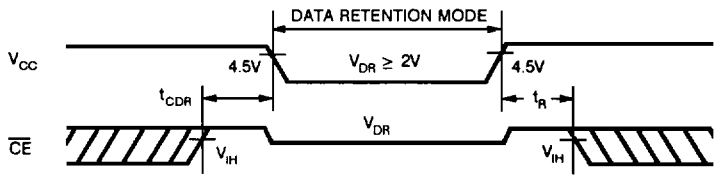
LOW V_{CC} DATA RETENTION WAVEFORM



AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	5ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
Output Load	See Figures 1, 2, & 3

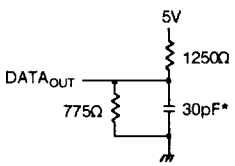


Figure 1. Output Load

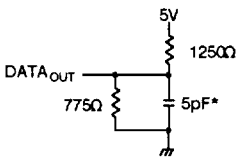


Figure 2. Output Load (for t_{LZ}, t_{HZ}, t_{WZ}, t_{OW})

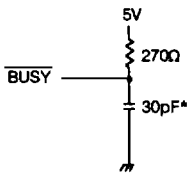


Figure 3. $\overline{BUSY}$ Output Load (IDT7133 only)

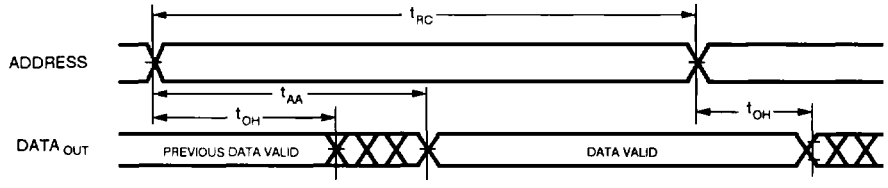
* Including scope and jig.

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

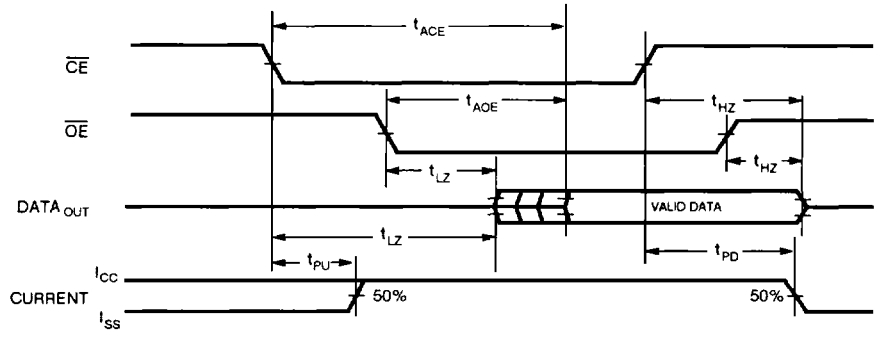
SYMBOL	PARAMETER	IDT7133S/L45 [2] IDT7143S/L45 [2] COM'L ONLY		IDT7133S/L55 IDT7143S/L55		IDT7133S/L70 IDT7143S/L70		IDT7133S/L90 IDT7143S/L90		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
READ CYCLE										
t_{RC}	Read Cycle Time	45	–	55	–	70	–	90	–	ns
t_{AA}	Address Access Time	–	45	–	55	–	70	–	90	ns
t_{ACE}	Chip Enable Access Time	–	45	–	55	–	70	–	90	ns
t_{AOE}	Output Enable Access Time	–	30	–	35	–	40	–	40	ns
t_{OH}	Output Hold From Address Change	0	–	0	–	0	–	10	–	ns
t_{LZ}	Output Low Z Time [1, 3]	5	–	5	–	5	–	5	–	ns
t_{HZ}	Output High Z Time [1, 3]	–	20	–	20	–	25	–	25	ns
t_{PU}	Chip Enable to Power Up Time [3]	0	–	0	–	0	–	0	–	ns
t_{PD}	Chip Disable to Power Down Time [3]	–	50	–	50	–	50	–	50	ns

NOTES:
1. Transition is measured ±500mV from low or high impedance voltage with load (see Figures 1, 2 & 3).
2. 0°C to +70°C temperature range only.
3. This parameter is guaranteed but not tested.

TIMING WAVEFORM OF READ CYCLE NO. 1, EITHER SIDE [1, 2, 4]



TIMING WAVEFORM OF READ CYCLE NO. 2, EITHER SIDE [1, 3]



NOTES:
1. R/$\overline{W}$ is high for Read Cycles.
2. Device is continuously enabled, $\overline{CE}$ = V_{IL}.
3. Addresses valid prior to or coincident with $\overline{CE}$ transition low.
4. $\overline{OE}$ = V_{IL}

AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

SYMBOL	PARAMETER	IDT7133S/L45[2] IDT7143S/L45[2] MIN.	MAX.	IDT7133S/L55 IDT7143S/L55 MIN.	MAX.	IDT7133S/L70 IDT7143S/L70 MIN.	MAX.	IDT7133S/L90 IDT7143S/L90 MIN.	MAX.	UNIT
WRITE CYCLE										
t_{WC}	Write Cycle Time[4]	45	–	55	–	70	–	90	–	ns
t_{EW}	Chip Enable to End of Write	30	–	40	–	50	–	85	–	ns
t_{AW}	Address Valid to End of Write	30	–	40	–	50	–	85	–	ns
t_{AS}	Address Setup Time	0	–	0	–	0	–	0	–	ns
t_{WP}	Write Pulse Width[6]	30	–	40	–	50	–	55	–	ns
t_{WR}	Write Recovery Time	0	–	0	–	0	–	0	–	ns
t_{DW}	Data Valid to End of Write	15	–	20	–	25	–	30	–	ns
t_{HZ}	Output High Z Time[1,3]	–	20	–	20	–	25	–	25	ns
t_{DH}	Data Hold Time[5]	5	–	5	–	5	–	5	–	ns
t_{WZ}	Write Enable to Output in High Z[1,3]	–	20	–	20	–	25	–	25	ns
t_{OW}	Output Active From End of Write[1,3,5]	5	–	5	–	5	–	5	–	ns

NOTES:

1. Transition is measured ±500mV from low or high impedance voltage with load (see Figures 1, 2 & 3).
2. 0°C to +70°C temperature range only.
3. This parameter is guaranteed but not tested.
4. For MASTER/SLAVE combination, $t_{WC} = t_{BAA} + t_{WR} + t_{WP}$.
5. The specification for t_{DH} must be met by the device supplying write data to the RAM under all operating conditions. Although t_{DH} and t_{OW} values will vary over voltage and temperature, the actual t_{DH} will always be smaller than the actual t_{OW}.
6. Specified for $\overline{OE}$ at high (Refer to "Timing Waveform of Write Cycle", Note 7).

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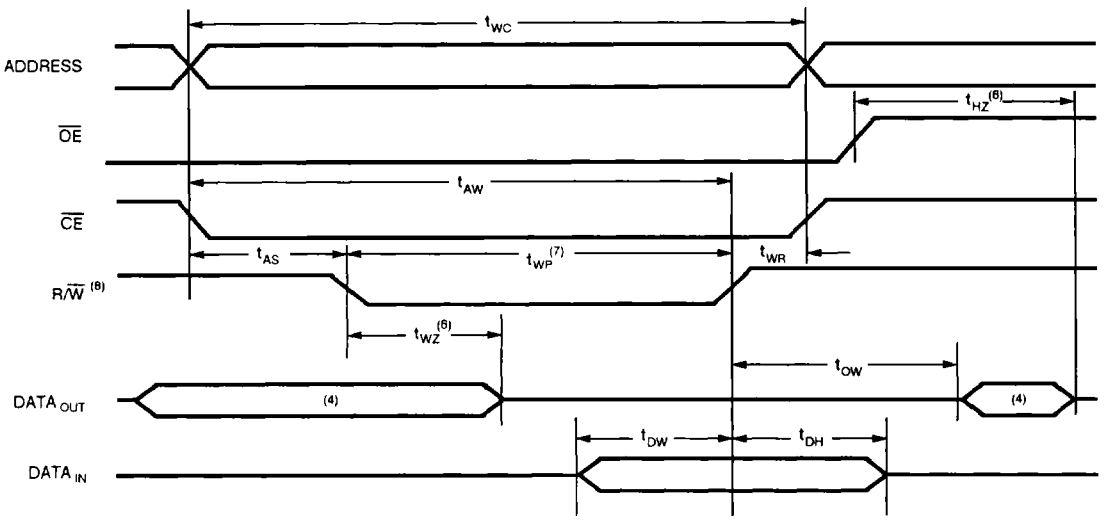
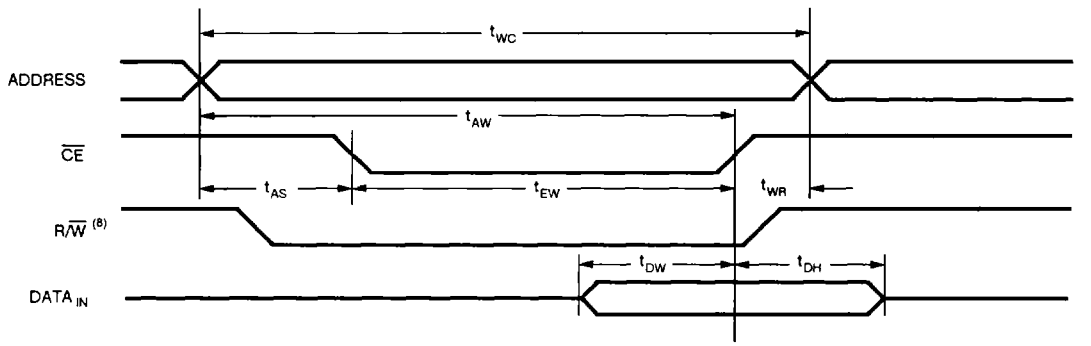
TIMING WAVEFORM OF WRITE CYCLE NO. 1 (R/$\overline{W}$ CONTROLLED TIMING) [1, 2, 3, 7]



WRITE CYCLE NO. 2 ($\overline{CE}$ CONTROLLED TIMING) [1, 2, 3, 5]



NOTES:

1. R/$\overline{W}$ or $\overline{CE}$ must be high during all address transitions.
2. A write occurs during the overlap (t_{EW} or t_{WP}) of a low $\overline{CE}$ and a low R/$\overline{W}$.
3. t_{WR} is measured from the earlier of $\overline{CE}$ or R/$\overline{W}$ going high to the end of write cycle.
4. During this period, the I/O pins are in the output state, and input signals must not be applied.
5. If the $\overline{CE}$ low transition occurs simultaneously with or after the R/$\overline{W}$ low transition, the outputs remain in the high impedance state.
6. Transition is measured ±500mV from steady state with a 5pF load (including scope and jig). This parameter is sampled and not 100% tested.
7. If $\overline{OE}$ is low during a R/$\overline{W}$ controlled write cycle, the write pulse width must be the larger of t_{WP} or (t_{WZ} + t_{DW}) to allow the I/O drivers to turn off and data to be placed on the bus for the required t_{DW}. If $\overline{OE}$ is high during an R/$\overline{W}$ controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified t_{WP}.
8. R/$\overline{W}$ for either upper or lower byte.

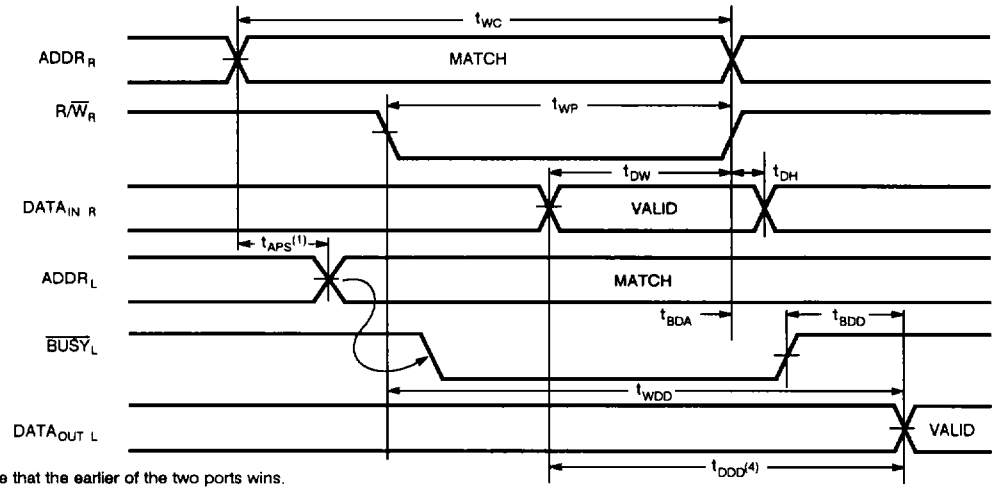
AC ELECTRICAL CHARACTERISTICS OVER THE OPERATING TEMPERATURE AND SUPPLY VOLTAGE

SYMBOL	PARAMETER	IDT7133S/L45[1] IDT7143S/L45[1] MIN.	MAX.	IDT7133S/L55 IDT7143S/L55 MIN.	MAX.	IDT7133S/L70 IDT7143S/L70 MIN.	MAX.	IDT7133S/L90 IDT7143S/L90 MIN.	MAX.	UNIT
BUSY TIMING (For MASTER IDT7133)										
t_{BAA}	$\overline{BUSY}$ Access Time to Address	–	45	–	50	–	55	–	55	ns
t_{BDA}	$\overline{BUSY}$ Disable Time to Address	–	40	–	40	–	45	–	45	ns
t_{BAC}	$\overline{BUSY}$ Access Time to Chip Enable	–	30	–	35	–	35	–	45	ns
t_{BDC}	$\overline{BUSY}$ Disable Time to Chip Enable	–	25	–	30	–	30	–	45	ns
t_{WDD}	Write Pulse to Data Delay[2]	–	80	–	80	–	90	–	100	ns
t_{DDD}	Write Data Valid to Read Data Delay[2]	–	55	–	55	–	70	–	90	ns
t_{BDD}	$\overline{BUSY}$ Disable to Valid Data[3]	–	Note 4	–	Note 4	–	Note 4	–	Note 4	ns
t_{APS}	Arbitration Priority Set Up Time[4]	5	–	5	–	5	–	10	–	ns
BUSY INPUT TIMING (For SLAVE IDT7143)										
t_{WB}	Write to $\overline{BUSY}$[5]	0	–	0	–	0	–	0	–	ns
t_{WH}	Write Hold After $\overline{BUSY}$[6]	30	–	30	–	30	–	30	–	ns
t_{WDD}	Write Pulse to Data Delay[7]	–	80	–	80	–	90	–	100	ns
t_{DDD}	Write Data Valid to Read Data Delay[7]	–	55	–	55	–	70	–	90	ns

NOTES:

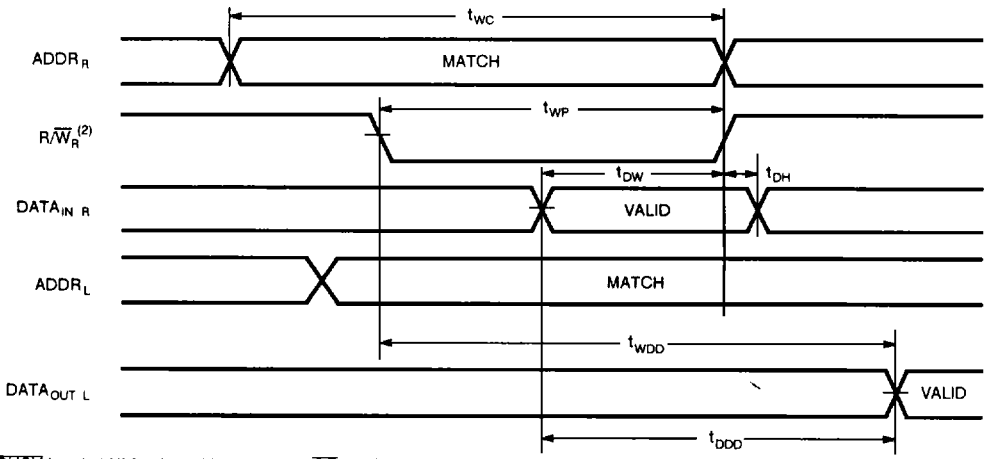
1. 0°C to +70°C temperature range only.
2. Port-to-port delay through RAM cells from writing port to reading port, refer to "TIMING WAVEFORM OF READ WITH BUSY (For Master IDT7133)"
3. t_{BDD} is calculated parameter and is greater of 0, $t_{WDD} - t_{WP}$ (actual) or $t_{DDD} - t_{DW}$ (actual).
4. To ensure that the earlier of the two ports wins.
5. To ensure that the write cycle is inhibited during contention.
6. To ensure that a write cycle is completed after contention.
7. Port-to-port delay through RAM cells from writing port to reading port, refer to "TIMING WAVEFORM OF READ WITH PORT-TO-PORT DELAY (For Slave IDT7143)"

TIMING WAVEFORM OF READ WITH $\overline{BUSY}$ (1, 2, 3)(For MASTER IDT7133)



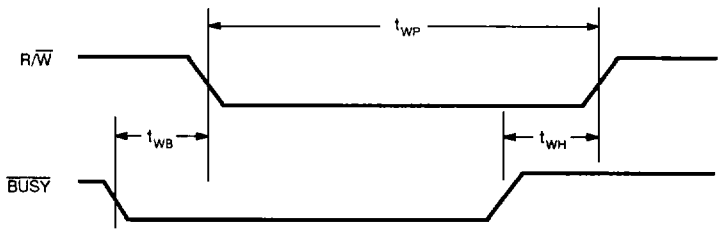
NOTES:
1. To ensure that the earlier of the two ports wins.
2. Write cycle parameters should be adhered to for ensuring proper writing.
3. Device is continously enabled for both ports.
4. $\overline{OE}$ at LO for the reading port.

TIMING WAVEFORM OF READ WITH PORT-TO-PORT DELAY (1, 2, 3)(For SLAVE IDT7143)



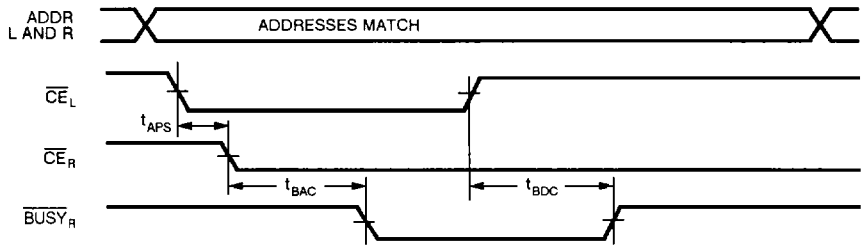
NOTES:
1. Assume $\overline{BUSY}$ input at HI for the writing port, and $\overline{OE}$ at LO for the reading port..
2. Write cycle parameters should be adhered to for ensuring proper writing.
3. Device is continously enabled for both ports.

TIMING WAVEFORM OF WRITE WITH $\overline{BUSY}$ INPUT (For SLAVE IDT7143)

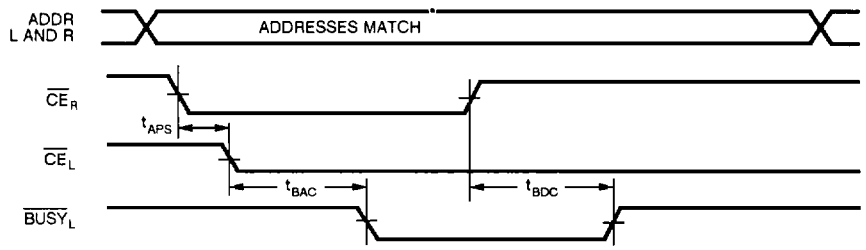


TIMING WAVEFORM OF CONTENTION CYCLE NO. 1, $\overline{CE}$ ARBITRATION

$\overline{CE}_L$ VALID FIRST:

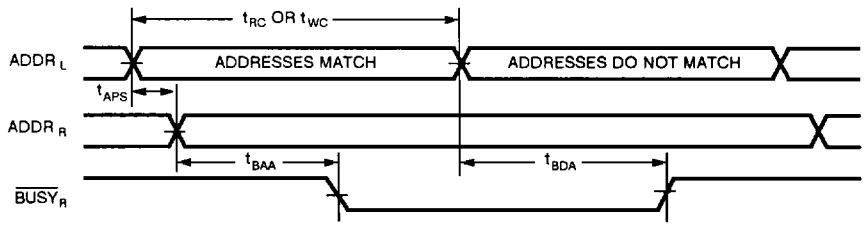


$\overline{CE}_R$ VALID FIRST:

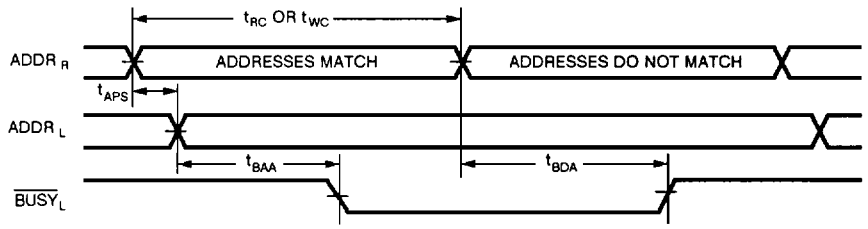


TIMING WAVEFORM OF CONTENTION CYCLE NO. 2, ADDRESS VALID ARBITRATION (1)

LEFT ADDRESS VALID FIRST:



RIGHT ADDRESS VALID FIRST:



NOTE:
1. $\overline{CE}_L = CE_R = V_{IL}$

FUNCTIONAL DESCRIPTION:

The IDT7133/43 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The devices have an automatic power down feature controlled by $\overline{CE}$. The $\overline{CE}$ controls on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE}$ high). When a port is enabled, access to the entire memory array is permitted. Each port has its own Output Enable control ($\overline{OE}$). In the read mode, the port's $\overline{OE}$ turns on the output drivers when set LOW. Non-contention READ/WRITE conditions are illustrated in Table I.

ARBITRATION LOGIC, FUNCTIONAL DESCRIPTION:

The arbitration logic will resolve an address match or a chip enable match down to 5ns minimum and determine which port has access. In all cases, an active $\overline{BUSY}$ flag will be set for the delayed port.

The $\overline{BUSY}$ flags are provided for the situation when both ports simultaneously access the same memory location. When this situation occurs, on-chip arbitration logic will determine which port has access and sets the delayed port's $\overline{BUSY}$ flag. $\overline{BUSY}$ is set at speeds that permit the processor to hold the operation and its respective address and data. It is important to note that the operation is invalid for the port that has $\overline{BUSY}$ set LOW. The delayed port will have access when $\overline{BUSY}$ goes inactive.

Contention occurs when both left and right ports are active and both addresses match. When this situation occurs, the on-chip arbitration logic determines access. Two modes of arbitration are provided: (1) if the addresses match and are valid before $\overline{CE}$, on-chip control logic arbitrates between $\overline{CE}_L$ and $\overline{CE}_R$ for access; or (2) if the $\overline{CE}$s are low before an address match, on-chip control logic arbitrates between the left and right addresses for access (refer to Table II). In either mode of arbitration, the delayed port's $\overline{BUSY}$ flag is set and will reset when the port granted access completes its operation.

DATA BUS WIDTH EXPANSION, MASTER/SLAVE DESCRIPTION:

Expanding the data bus width to 32 bits or more in a dual-port RAM system implies that several chips will be active at the same time. If each chip includes a hardware arbitrator, and the addresses for each chip arrive at the same time, it is possible that one will activate its $\overline{BUSY}_L$ while another activates its $\overline{BUSY}_R$ signal. Both sides are now busy and the CPUs will wait indefinitely for their port to become free.

To avoid this "Busy Lock-Out" problem, IDT has developed a MASTER/SLAVE approach where only one hardware arbitrator, in the MASTER, is used. The SLAVE has $\overline{BUSY}$ inputs which allow an interface to the MASTER with no external components and with a speed advantage over other systems.

When expanding dual-port RAMs in width, the writing of the SLAVE RAMs must be delayed until after the $\overline{BUSY}$ input has settled. Otherwise, the SLAVE chip may begin a write cycle during a contention situation. Conversely, the write pulse must extend a hold time past $\overline{BUSY}$ to ensure that a write cycle takes place after the contention is resolved. This timing is inherent in all dual-port memory systems where more than one chip is active at the same time.

The write pulse to the SLAVE should be delayed by the maximum arbitration time of the MASTER. If, then, a contention occurs, the write to the SLAVE will be inhibited due to $\overline{BUSY}$ from the MASTER.

TABLE I—NON-CONTENTION READ/WRITE CONTROL[4]

LEFT OR RIGHT PORT [1]						FUNCTION
$R/\overline{W}_{LB}$	$R/\overline{W}_{UB}$	$\overline{CE}$	$\overline{OE}$	I/O_{0-7}	I/O_{8-15}	
X	X	H	X	Z	Z	Port Disabled and In Power Down mode, I_{SB2} or I_{SB4}
X	X	H	X	Z	Z	$\overline{CE}_R = \overline{CE}_L$ = H, Power Down Mode, I_{SB1} or I_{SB3}
L	L	L	X	$DATA_{IN}$	$DATA_{IN}$	Data on Lower Byte and Upper Byte Written into Memory[2]
L	H	L	L	$DATA_{IN}$	$DATA_{OUT}$	Data on Lower Byte Written into Memory,[2] Data In Memory Output on Upper Byte[3]
H	L	L	L	$DATA_{OUT}$	$DATA_{IN}$	Data in Memory Output on Lower Byte;[3] Data on Upper Byte Written Into Memory[2]
L	H	L	H	$DATA_{IN}$	Z	Data on Lower Byte Written into Memory[2]
H	L	L	H	Z	$DATA_{IN}$	Data on Upper Byte Written into Memory[2]
H	H	L	L	$DATA_{OUT}$	$DATA_{OUT}$	Data in Memory Output on Lower Byte and Upper Byte[3]
H	H	L	H	Z	Z	High Impedance Outputs

NOTES:

1. $A_{0L} - A_{10L} \neq A_{0R} - A_{10R}$
2. If $\overline{BUSY}$ = L, data is not written.
3. If $\overline{BUSY}$ = L, data may not be valid, see t_{WDD} and t_{DDD} timing.
4. H = High, L = Low, X = Don't Care, Z = High Impedance, LB = Lower Byte, UB = Upper Byte

TABLE II – ARBITRATION

LEFT PORT		RIGHT PORT		FLAGS[1]		FUNCTION
$\overline{CE}_L$	$A_{0L} - A_{10L}$	$\overline{CE}_R$	$A_{0R} - A_{10R}$	$\overline{BUSY}_L$	$\overline{BUSY}_R$	
H	X	H	X	H	H	No Contention
L	Any	H	X	H	H	No Contention
H	X	L	Any	H	H	No Contention
L	$\neq A_{0R} - A_{10R}$	L	$\neq A_{0L} - A_{10L}$	H	H	No Contention
ADDRESS ARBITRATION WITH $\overline{CE}$ LOW BEFORE ADDRESS MATCH						
L	LV5R	L	LV5R	H	L	L-Port Wins
L	RV5L	L	RV5L	L	H	R-Port Wins
L	Same	L	Same	H	L	Arbitration Resolved
L	Same	L	Same	L	H	Arbitration Resolved
$\overline{CE}$ ARBITRATION WITH ADDRESS MATCH BEFORE $\overline{CE}$						
LL5R	$= A_{0R} - A_{10R}$	LL5R	$= A_{0L} - A_{10L}$	H	L	L-Port Wins
RL5L	$= A_{0R} - A_{10R}$	RL5L	$= A_{0L} - A_{10L}$	L	H	R-Port Wins
LW5R	$= A_{0R} - A_{10R}$	LW5R	$= A_{0L} - A_{10L}$	H	L	Arbitration Resolved
LW5R	$= A_{0R} - A_{10R}$	LW5R	$= A_{0L} - A_{10L}$	L	H	Arbitration Resolved

NOTE:

1. X = Don't Care, L = Low, H = High
   LV5R = Left Address Valid ≥ 5ns before right address
   RV5L = Right Address Valid ≥ 5ns before left address
   Same = Left and Right Address match within 5ns of each other
   LL5R = Left $\overline{CE}$ = LOW ≥ 5ns before Right $\overline{CE}$
   RL5L = Right $\overline{CE}$ = LOW ≥ 5ns before Left $\overline{CE}$
   LW5R = Left and Right $\overline{CE}$ = LOW within 5ns of each other

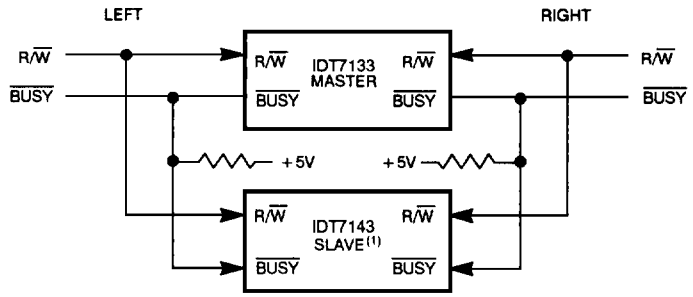
CAPACITANCE (T_A = +25°C, f = 1.0MHz)

SYMBOL	PARAMETER[1]	CONDITIONS	MAX.	UNIT
C_{IN}	Input Capacitance	V_{IN} = 0V	11	pF
C_{OUT}	Input/Output Capacitance	$V_{I/O}$ = 0V	11	pF

NOTE:

1. This parameter is determined by device characterization but is not production tested.

32-BIT MASTER/SLAVE DUAL-PORT MEMORY SYSTEMS



NOTE:

1. No arbitration in IDT7143 (SLAVE). $\overline{BUSY}$-IN inhibits write in IDT7143 (SLAVE).

ORDERING INFORMATION